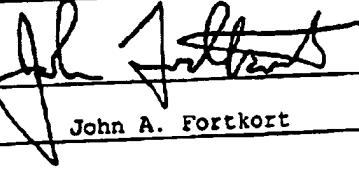
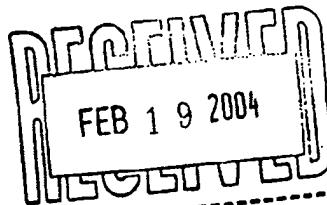


In re Application of: Sadaka et al.
Serial No.: 10/029,903
Filing Date: 12/21/01
Examiner: Pham Long
Art Unit: 2814
Title: A CHEMISTRY FOR ETCHING QUATERNARY INTERFACE LAYERS ON InGaAsP MOSTLY FORMED BETWEEN GaAs AND In_xGa_(1-x)P LAYERS

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

CERTIFICATION OF FACSIMILE TRANSMISSION	
I hereby certify that this paper is being transmitted via facsimile to the Patent and Trademark Office on the date shown below.	
January 3, 2004	
Date	
Signature	
Printed Name	John A. Fortkort



RESPONSE TO OFFICE ACTION

Dear Sir:

In response to the Office Action dated October 3, 2003,
Applicant hereby responds as follows.

Amendments to the Specification: No amendments to the specification are included with this response.

Amendments to the Claims: are reflected in the listing of claims which begins on Page 3 of this paper.

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good selectivity to InGaP is obtained. The claimed subject matter is patentable over the prior art, because neither reference recognizes the criticality of HCl/H₂O₂ concentrations in achieving selectivity to InGaP.

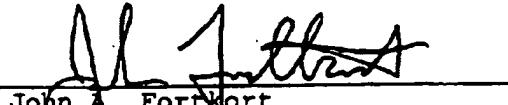
With respect to new claim 42 added with this response, Applicants respectfully note that support for this claim can be found, for example, in the paragraph immediately following TABLE 2. This limitation is significant, because it was Applicants' surprising discovery that the etch used to remove the InGaAsP formations could be made highly selective to InGaP when the components of the etch were controlled within certain ranges of volume ratios or mole ratios (and that, conversely, when the components of the etch fell outside of these ranges, selectivity to InGaP was seen to suffer).

Please charge any payment due with this response (including the payment for additional claims) or credit any overpayment to the deposit account of Hulsey, Grether, Fortkort & Webster, LLP, Deposit Account No. 50-2726. Please reference our docket No. MTRL002USO.

Respectfully submitted,

HULSEY, GRETHER,
FORTKORT & WEBSTER, LLP

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Dated: January 3, 2004

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